

FS70SM-06

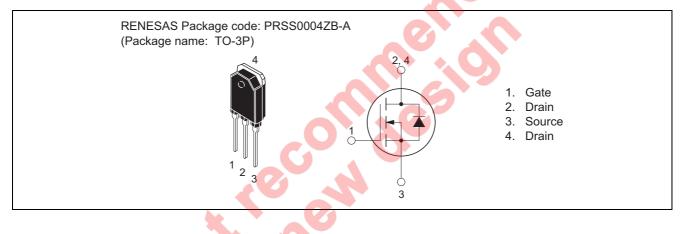
High-Speed Switching Use Nch Power MOS FET

REJ03G1430-0200 (Previous: MEJ02G0099-0101) Rev.2.00 Aug 07, 2006

Features

- Drive voltage : 10 V
- V_{DSS} : 60 V
- $r_{\text{DS(ON)}(\text{max})}$: 7.5 m Ω
- I_D: 70 A
- Integrated Fast Recovery Diode (TYP.): 85 ns

Outline



Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

		$(\mathrm{Tc} = 25^{\circ}\mathrm{C})$		
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	60	V	$V_{GS} = 0 V$
Gate-source voltage	V _{GSS}	±20	V	$V_{DS} = 0 V$
Drain current	I _D	70	А	
Drain current (Pulsed)	I _{DM}	280	А	
Avalanche drain current (Pulsed)	I _{DA}	70	А	L = 100 μH
Source current	Is	70	А	
Source current (Pulsed)	I _{SM}	280	А	
Maximum power dissipation	PD	150	W	
Channel temperature	Tch	– 55 to +150	°C	
Storage temperature	Tstg	– 55 to +150	°C	
Mass	_	4.8	g	Typical value

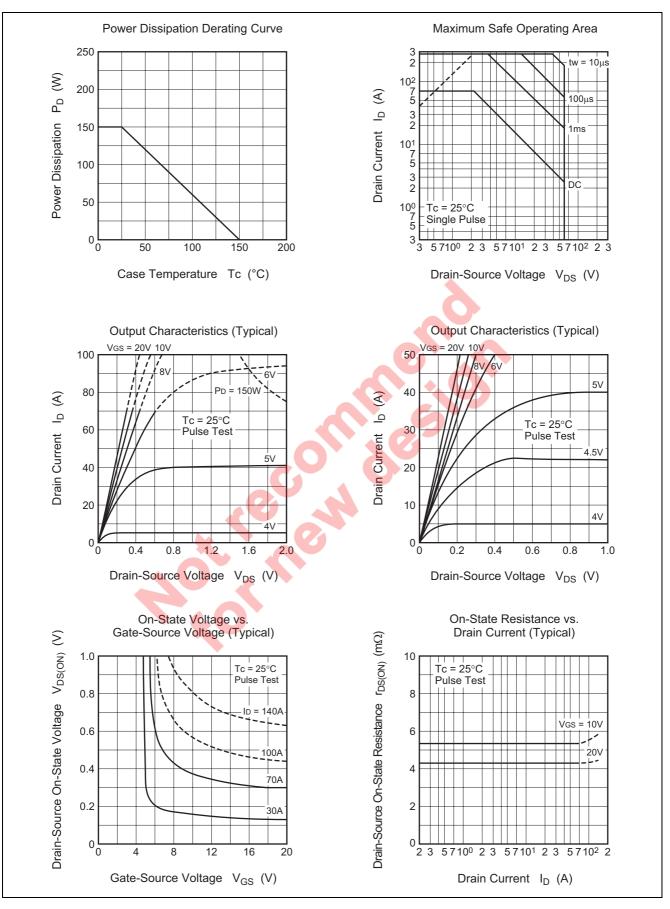


Electrical Characteristics

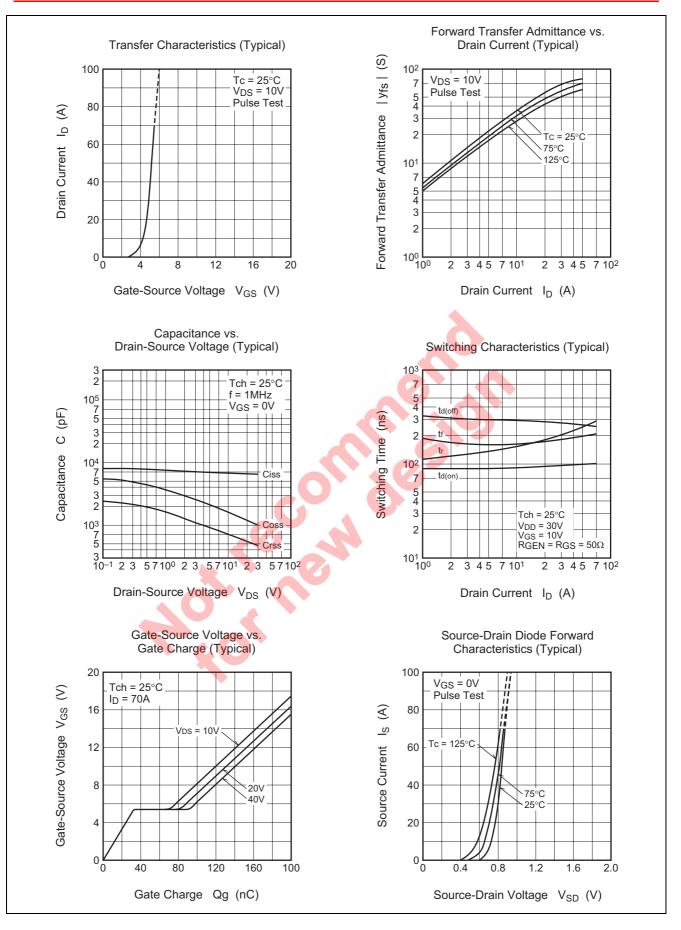
	$(Tch = 25^{\circ}C)$							
Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions		
Drain-source breakdown voltage	V _{(BR)DSS}	60	—	—	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$		
Gate-source leakage current	I _{GSS}	—	—	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		
Drain-source leakage current	I _{DSS}	_	—	0.1	mA	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$		
Gate-source threshold voltage	V _{GS(th)}	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$		
Drain-source on-state resistance	r _{DS(ON)}	_	5.7	7.5	mΩ	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}$		
Drain-source on-state voltage	V _{DS(ON)}	_	0.200	0.263	V	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}$		
Forward transfer admittance	y _{fs}	50	70	_	S	$I_D = 35 \text{ A}, V_{DS} = 10 \text{ V}$		
Input capacitance	Ciss	_	6540	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		
Output capacitance	Coss	_	1640	_	pF	f = 1MHz		
Reverse transfer capacitance	Crss	_	790	—	pF			
Turn-on delay time	t _{d(on)}	_	95	—	ns	$V_{DD} = 30 \text{ V}, I_D = 35 \text{ A},$		
Rise time	tr		195		ns	V_{GS} = 10 V, R _{GEN} = R _{GS} = 50 Ω		
Turn-off delay time	t _{d(off)}	_	290	—	ns			
Fall time	t _f	_	210	—	ns			
Source-drain voltage	V _{SD}	_	1.0	1.5	V	$I_{S} = 35 \text{ A}, V_{GS} = 0 \text{ V}$		
Thermal resistance	R _{th(ch-c)}	_	—	0.83	°C/W	Channel to case		
Reverse recovery time	t _{rr}		85		ns	$I_{\rm S} = 70$ A, $d_{\rm is}/d_{\rm t} = -100$ A/ μ s		



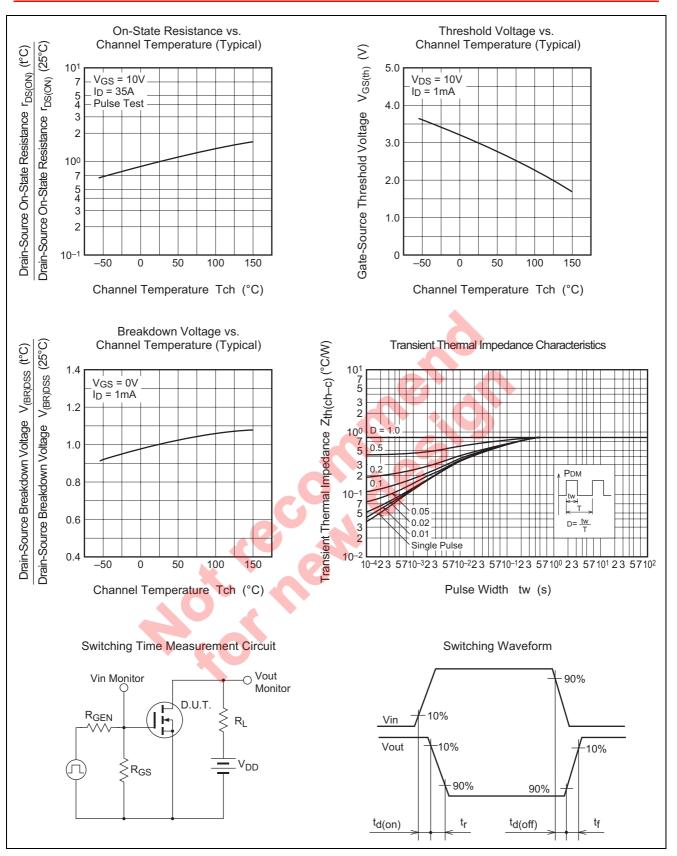
Performance Curves



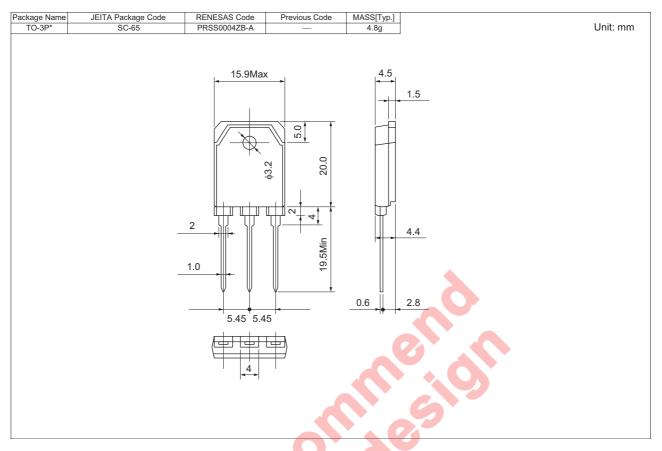








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Static electricity prevention bag	20	Type name	FS70SM-06
Lead form	Plastic Magazine (Tube)	30	Type name – Lead forming code	FS70SM-06-A8

Note : Please confirm the specification about the shipping in detail.

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